SPICE Device Model SiZ900DT



Vishay Siliconix

Dual N-Channel 30 V (D-S) MOSFET

DESCRIPTION

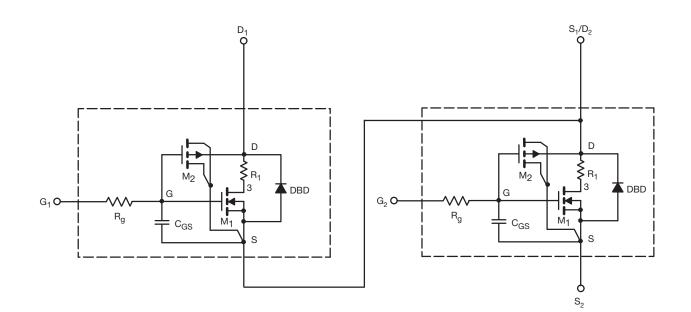
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched Cgd model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC

CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the 55 °C to + 125 °C Temperature Range
- · Model the Gate Charge, Transient, and Diode Reverse **Recovery Characteristics**



Note

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS		SIMULATED DATA	MEASURED DATA	UNIT
Static	•	•				
Gate Threshold Voltage	V _{GS(th)}	V_{DS} = V_{GS} , I_D = 250 μ A	Ch-1	1.9	-	V
			Ch-2	1.8	-	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 19.4 A	Ch-1	0.0061	0.0059	Ω
		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	Ch-2	0.0032	0.0032	
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 17.2 \text{ A}$	Ch-1	0.0075	0.0075	
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	Ch-2	0.0039	0.0038	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 19.4 \text{ A}$	Ch-1	64	76	S
		$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	Ch-2	90	120	
Diode Forward Voltage ^a	V _{SD}	I _S = 10 A	Ch-1	0.80	0.80	V
			Ch-2	0.80	0.80	
Dynamic ^b		•				
Input Capacitance	C _{iss}		Ch-1	1820	1830	ρF
		$\label{eq:channel-1} \begin{array}{l} Channel-1\\ V_{DS}=15 \text{ V}, \text{ V}_{GS}=0 \text{ V}, \text{ f}=1 \text{ MHz}\\ \\ Channel-2\\ \text{ V}_{DS}=15 \text{ V}, \text{ V}_{GS}=0 \text{ V}, \text{ f}=1 \text{ MHz} \end{array}$	Ch-2	4850	4900	
Output Capacitance	C _{oss}		Ch-1	303	300	
			Ch-2	719	710	
Reverse Transfer Capacitance	C _{rss}		Ch-1	123	120	
			Ch-2	289	280	
Total Gate Charge	Qg	Channel-1 $V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 19.4 \text{ A}$	Ch-1	28	29	nC
		$\begin{array}{l} \mbox{Channel-2} \\ \mbox{V}_{DS} = 15 \mbox{ V}, \mbox{ V}_{GS} = 10 \mbox{ V}, \mbox{ I}_{D} = 20 \mbox{ A} \end{array}$	Ch-2	73	73	
		Channel-1 $V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 19.4 \text{ A}$ Channel-2 $V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	Ch-1	14	13.5	
			Ch-2	35	34	
Gate-Source Charge	Q _{gs}		Ch-1	5.8	5.8	
			Ch-2	15	15	
Gate-Drain Charge	Q _{gd}		Ch-1	3.1	3.1	
			Ch-2	7.3	7.3	

Notes

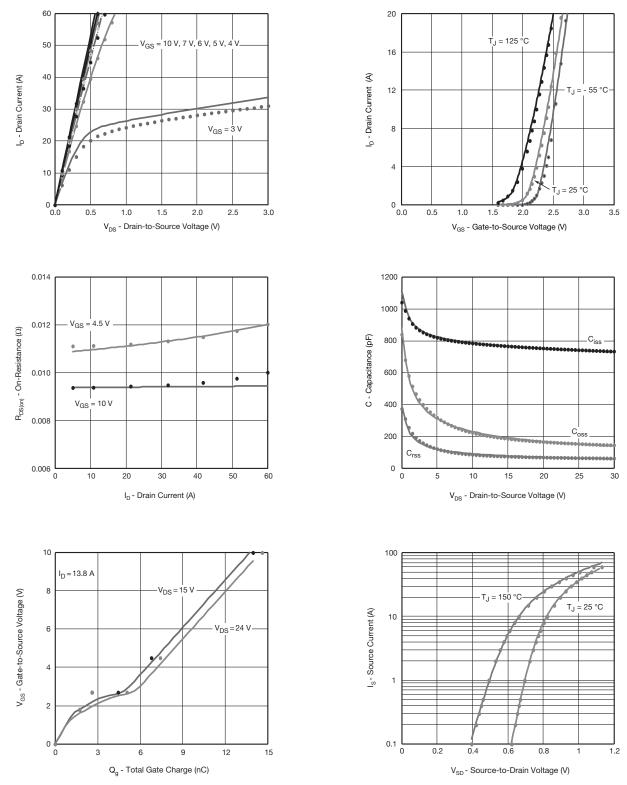
a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.



COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 $^\circ\text{C},$ unless otherwise noted)

Channel-1 MOSFET



Note

• Dots and squares represent measured data.

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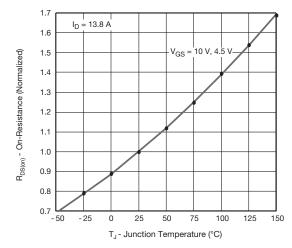
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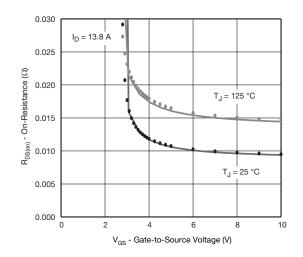




COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C, unless otherwise noted)

Channel-1 MOSFET





Note

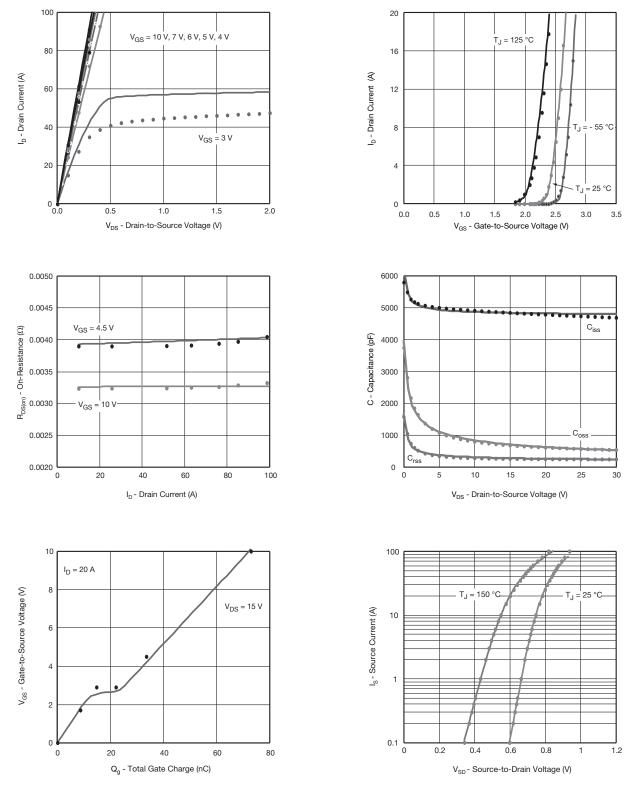
Dots and squares represent measured data.





COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 $^\circ\text{C},$ unless otherwise noted)

Channel-2 MOSFET



Note

• Dots and squares represent measured data.

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